Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	99763	((flash volatile (non-volatile)) near3 memory)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:28
L4	82772	eeprom eprom prom e2prom	US-PGPUB; USPAT	OR	ON	2004/11/14 17:28
L5	142076	3 4	US-PGPUB; USPAT	OR	ON	2004/11/14 17:15
L6	72685	5 and (trench recess grove hole open$4)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:26
L7	13072	6 and ((select control) near5 gate)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:28
L8	7481	7 and (float$3 near5 gate)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:29
L9	7284	8 and (source drain)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:26
L10	3412	9 and (ONO (oxide near3 nitride near3 oxide))	US-PGPUB; USPAT	OR	ON	2004/11/14 17:27
L11	3336	10 and (insulat$3 dielectric)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:19
L12	1089	11 and (resist photoreisit PR)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:20
L13	1089	12 and (etch$3 pattern$4)	US-PGPUB; USPAT	OR	ON	2004/11/14 17:20
L14	39400	((flash volatile (non-volatile)) near3 memory)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:28
L15	27547	eeprom eprom prom e2prom	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:25
L16	60866	14 15	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:25
L17	3796	16 and (trench recess grove hole open$4)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:26
L18	973	17 and ((select control) near5 gate)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:26
L19	846	18 and (float$3 near5 gate)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:26
L20	503	19 and (source drain)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:27

L21	41	20 and (ONO (oxide near3 nitride near3 oxide))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/14 17:27
L22	29	((flash volatile (non-volatile)) near3 memory)	USOCR	OR	ON	2004/11/14 17:28
L23	9429	eeprom eprom prom e2prom	USOCR	OR	ON	2004/11/14 17:28
L24	9457	22 23	USOCR	OR	ON .	2004/11/14 17:28
L25	105	24 and ((select control) near5 gate)	USOCR	OR	ON	2004/11/14 17:29
L26	6	24 and (float$3 near5 gate)	USOCR	OR	ON	2004/11/14 17:29